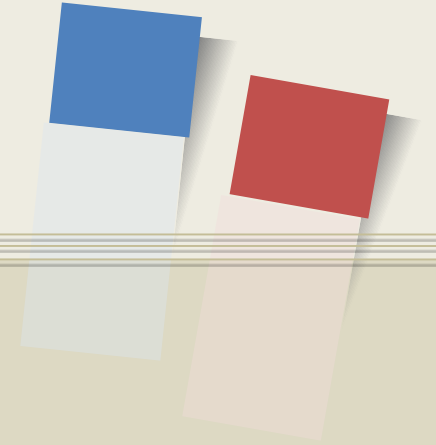


2012142030 신윤철



# PMOS

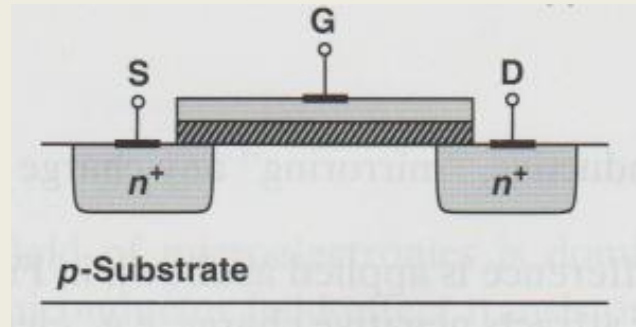




# MOS Device Type(1)

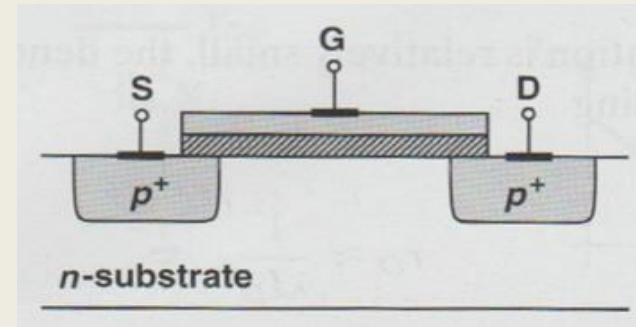


## <NMOS>



- $V_G > V_S$
- $V_{TH} > 0$
- $V_D > V_S$

## <PMOS>



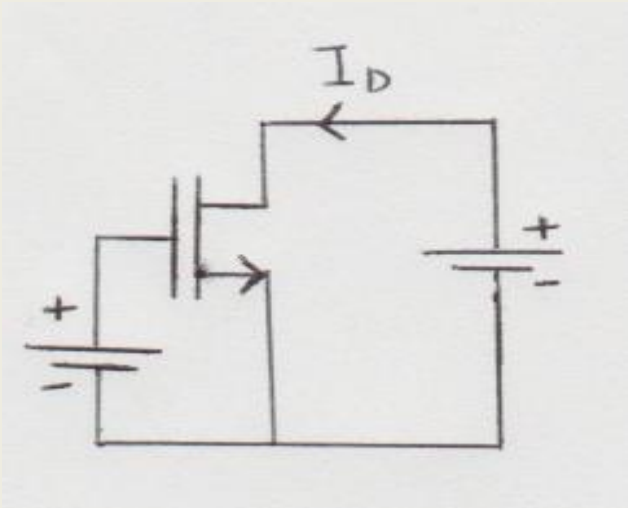
- $V_G < V_S$
- $V_{TH} < 0$
- $V_D < V_S$

- To turn on the PMOS device,  $V_{GS} < V_{TH}$

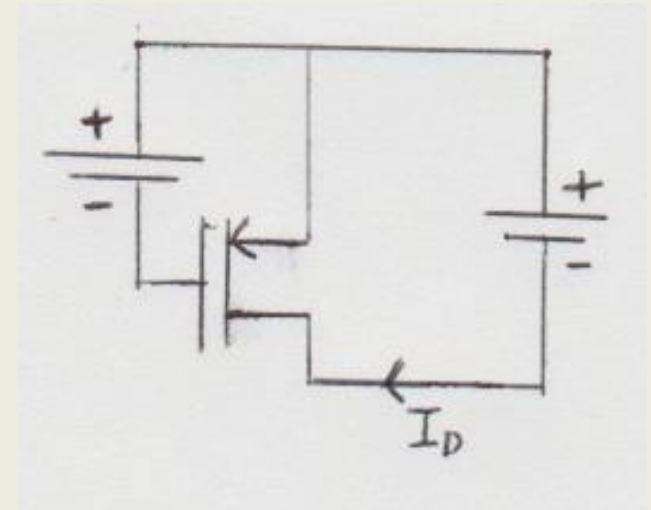
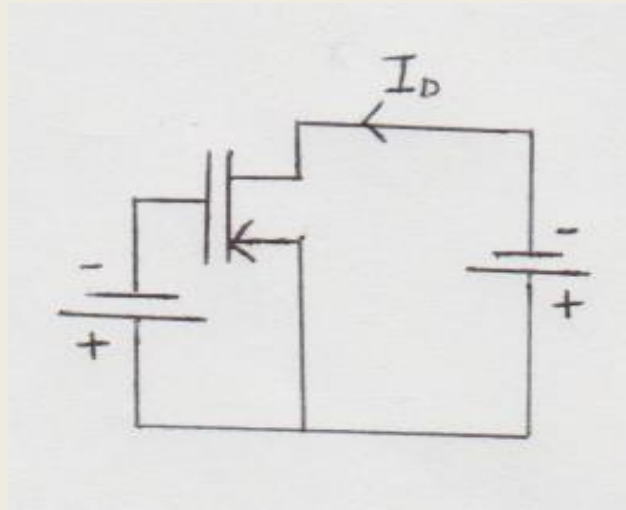


# MOS Device Type(2)

<NMOS>



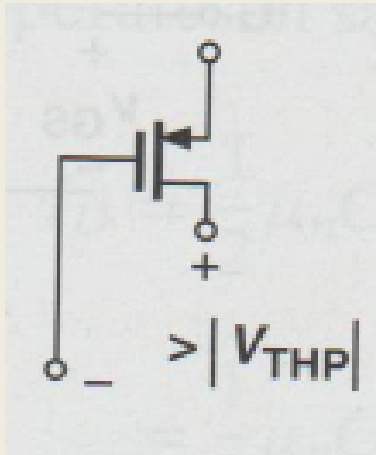
<PMOS>



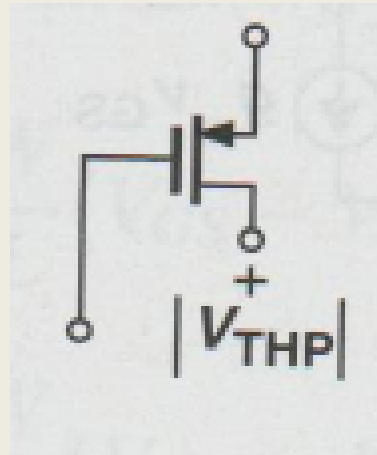
- In saturation :  $I_D = -\frac{1}{2}\mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2 (1 - \lambda V_{DS})$  ( $\lambda > 0$ )



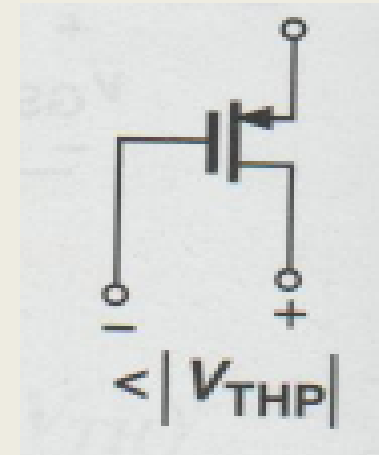
# MOS Device Type(3)



Triode



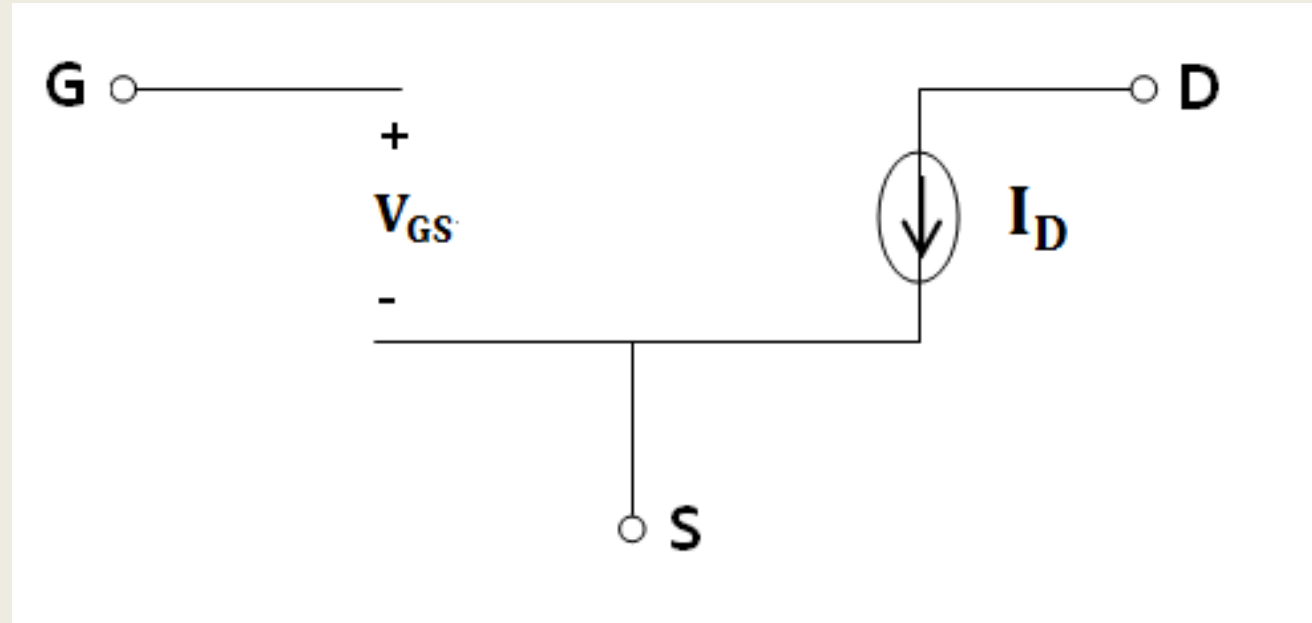
Edge



Saturation



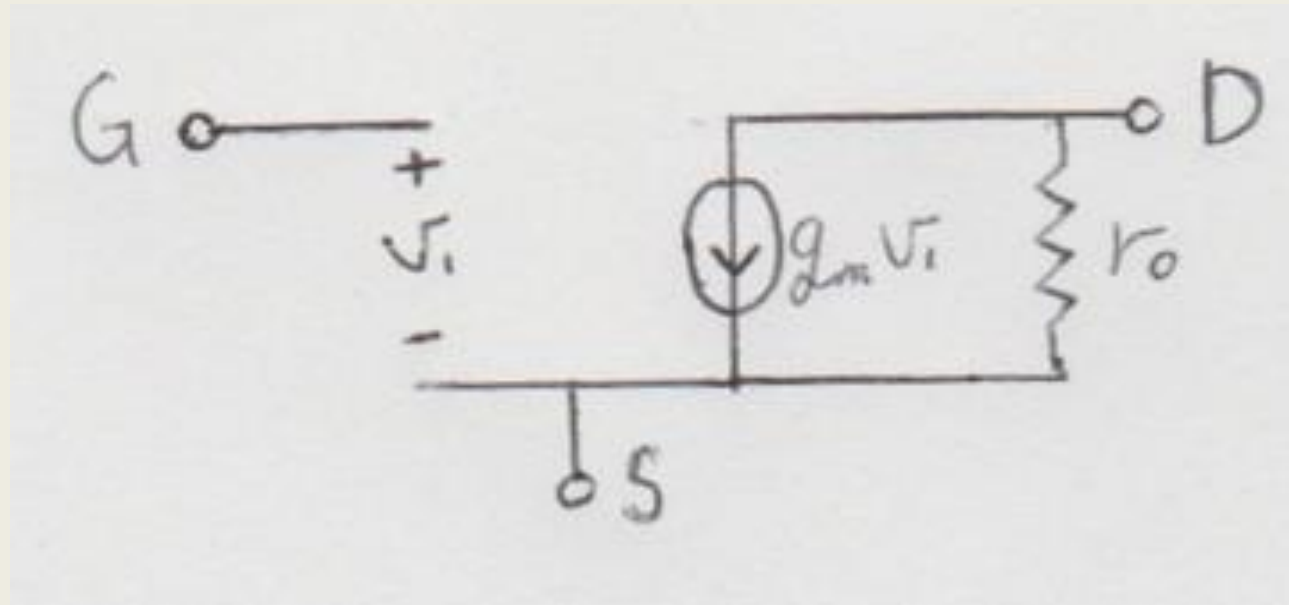
# PMOS – Large-signal model





# PMOS – Small-signal model(1)

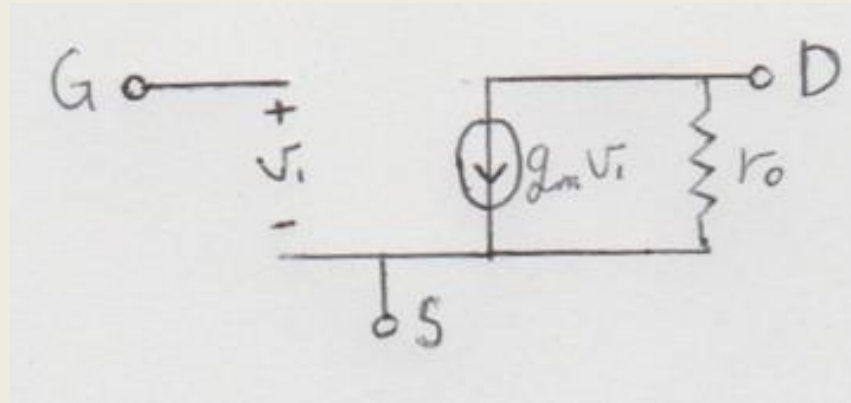
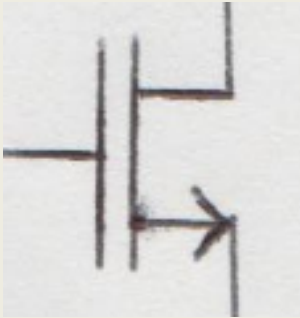
- *Identical* to the small-signal model of NMOS.



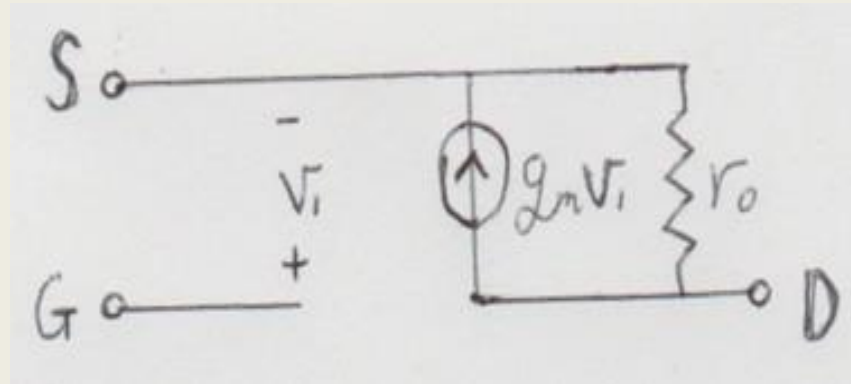


# PMOS – Small-signal model(2)

<NMOS>

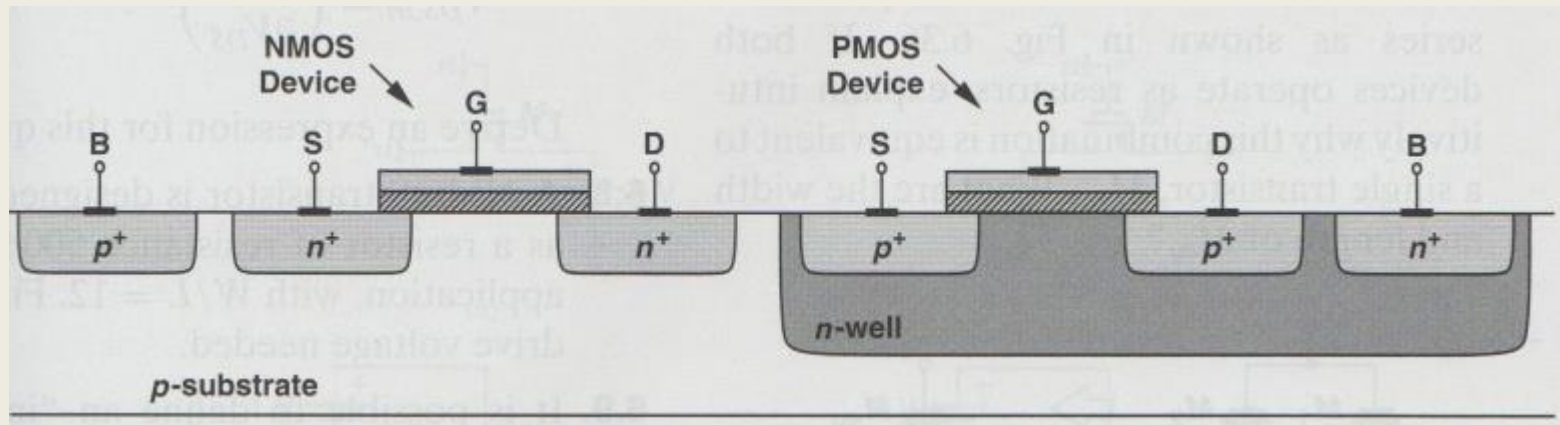
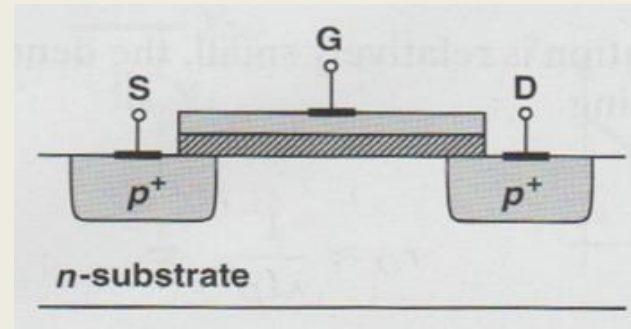
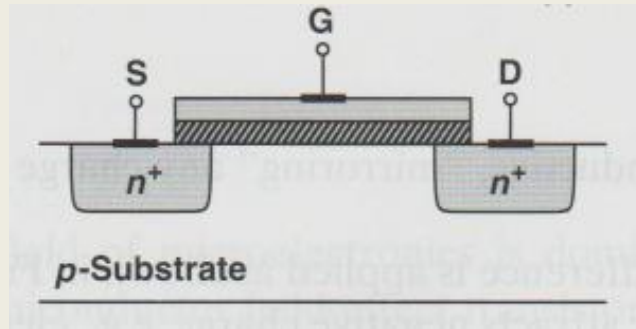


<PMOS>

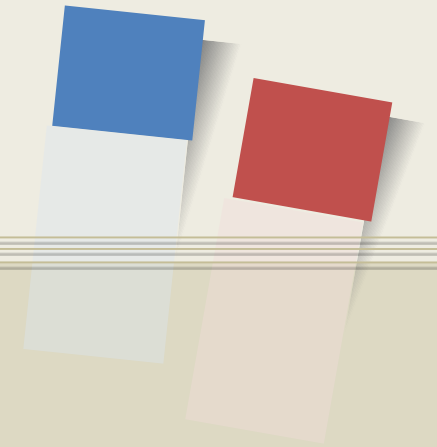




# CMOS Technology







**Thank you**

